

isc Thyristors

MCR100-6RLG

FEATURES

- With TO-92 package
- Sensitive gate trigger current
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

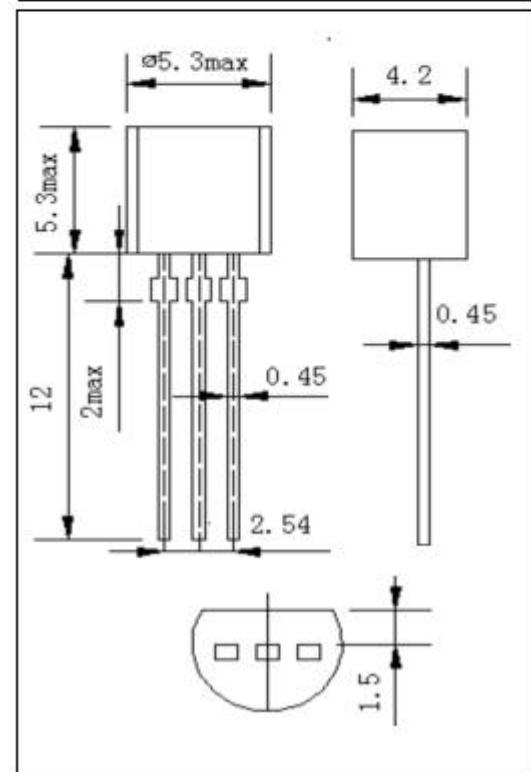
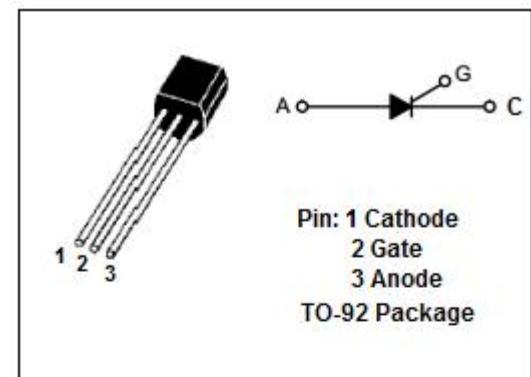
- Designed for high volume, line-powered consumer applications such as relay and lamp drivers, small motor controls, gate drivers for larger thyristors, and sensing and detection circuits.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DRM}	Repetitive peak off-state voltage	400	V
V_{RRM}	Repetitive peak off-state voltage	400	V
$I_{T(RMS)}$	RMS on-state current(180° conduction angle)	0.8	A
I_{TSM}	Non-repetitive peak on-state current($(tp=10\text{ms})$)	10	A
I_{GM}	Peak gate current($(tp=20\text{ }\mu\text{s})$)	1	A
I^2t	$I^2t(tp=10\text{ms})$	0.415	A^2s
P_{GM}	Peak gate power	2	W
$P_{G(AV)}$	Average gate power	0.1	W
T_j	Operating junction temperature	-40-100	$^\circ\text{C}$
T_{stg}	Storage temperature range	-40-150	$^\circ\text{C}$

Thermal resistance

SYMBOL	PARAMETER	MAX	UNIT
$R_{th}(j-c)$	Junction to case	75	k/W
$R_{th}(j-a)$	Junction to ambient air	200	k/W



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ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
I_{RRM}	Repetitive peak reverse current	$V_R = V_{RRM}$ $V_R = V_{RRM}; T_j = 110^\circ\text{C}$			10 100	$\mu\text{ A}$
I_{DRM}	Repetitive peak off-state current	$V_D = V_{DRM}$ $V_D = V_{DRM}; T_j = 110^\circ\text{C}$			10 100	$\mu\text{ A}$
I_{GT}	Gate trigger current	$V_D = 7\text{V}; R_L = 100 \Omega$			200	$\mu\text{ A}$
V_{TM}	On-state voltage	$I_T = 1.0\text{A}, t_p = 380 \mu\text{s}$			1.7	V
I_H	Holding current	$I_T = 0.1\text{A}$, Gate Open		1	5	mA
V_{GT}	Gate trigger voltage	$V_D = 7\text{V}; R_L = 100 \Omega$			0.8	V